

ABSTRACT

The disclosure relates to methods and solutions for precisely and rapidly etching a polyimide resin layer.

5 Etching solutions of the present invention include 3-65 % by weight of a diol containing 3 to 6 carbon atoms or a triol containing 4 to 6 carbon atoms, 10-55 % by weight of an alkali compound and water in an amount of 0.75-3.0 times the amount of the alkali compound, and can be used at 65 °C or more to
10 rapidly etch a polyimide resin layer having an imidation degree of 50-98 % without unfavorably affecting the working atmosphere. Even if the resin layer is completely imidated after etching, the etching pattern of the resulting resin layer is not deformed with a decreased contamination by
15 impurity ions as compared with those obtained using conventional etching solutions.

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